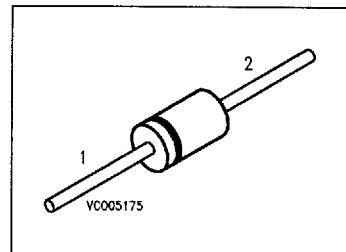


## Silicon Variable Capacitance Diode

BB 409

- For VHF tuners
- Not for new design



| Type   | Marking | Ordering Code | Pin Configuration | Package <sup>1)</sup> |
|--------|---------|---------------|-------------------|-----------------------|
| BB 409 | green   | Q62702-B112   |                   | DO-35 DHD             |

### Maximum Ratings

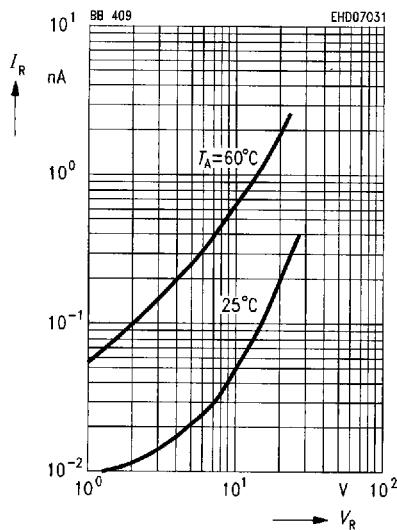
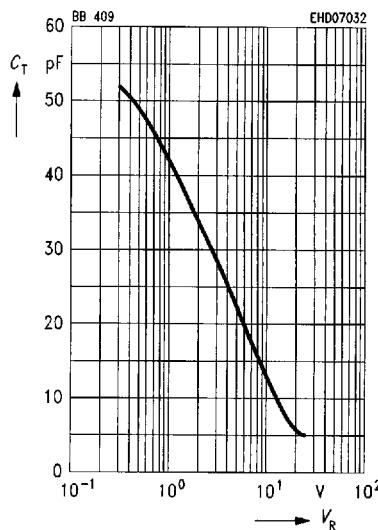
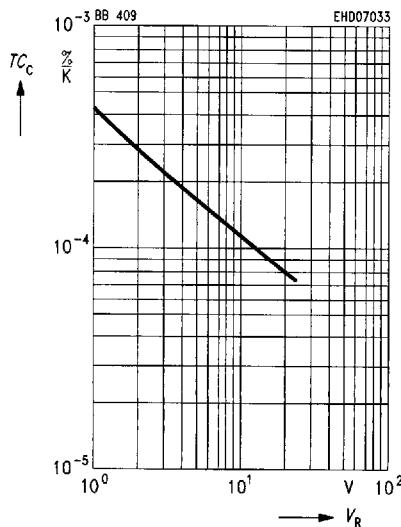
| Parameter                                    | Symbol    | Values         | Unit |
|--|-----------|----------------|------|
| Reverse voltage                              | $V_R$     | 28             | V    |
| Peak reverse voltage                         | $V_{RM}$  | 30             |      |
| Forward current, $T_A \leq 60^\circ\text{C}$ | $I_F$     | 20             | mA   |
| Storage temperature range                    | $T_{stg}$ | - 55 ... + 150 | °C   |

<sup>1)</sup> For detailed information see chapter Package Outlines.

**Electrical Characteristics**at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

| Parameter  | Symbol                   | Values    |  |           | Unit                |
|--|--------------------------|-----------|--|-----------|---------------------|
|  |                          | min.      | typ.                                       | max.      |                     |
| Reverse current<br>$V_R = 28\text{ V}$<br>$V_R = 28\text{ V}, T_A = 60^\circ\text{C}$                            | $I_R$                    | —<br>—    | —<br>—                                     | 50<br>0.5 | nA<br>$\mu\text{A}$ |
| Diode capacitance, $f = 1\text{ MHz}$<br>$V_R = 3\text{ V}$<br>25 V  | $C_T$                    | 26<br>4.5 | —<br>—                                     | 32<br>5.6 | pF                  |
| Capacitance ratio<br>$V_R = 3\text{ V}, 25\text{ V}, f = 1\text{ MHz}$   | $\frac{C_{T3}}{C_{T25}}$ | 5         | —  | 6.5       | —                   |
| Capacitance matching<br>$V_R = 1\text{ V} \dots 28\text{ V}$   | $\frac{\Delta C_T}{C_T}$ | —         | —  | 3         | %                   |
| Series resistance<br>$C_T = 12\text{ pF}, f = 100\text{ MHz}$  | $r_s$                    | —         | 0.3  | —         | $\Omega$            |
| Q factor<br>$V_R = 3\text{ V}, f = 50\text{ MHz}$<br>$V_R = 25\text{ V}, f = 200\text{ MHz}$                     | $Q$                      | —<br>—    | 280<br>600                                 | —<br>—    | —                   |
| Series inductance  | $L_s$                    | —         | 3  | —         | nH                  |
| Temperature coefficient of<br>diode capacitance, $f = 1\text{ MHz}$<br>$V_R = 3\text{ V}$<br>$V_R = 25\text{ V}$ | $TC_c$                   | —<br>—    | $2.5 \cdot 10^{-4}$<br>$0.8 \cdot 10^{-4}$ | —<br>—    | 1/K                 |

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**Reverse current  $I_R = f(V_R)$** **Diode capacitance  $C_T = f(V_R)$** **Temperature coefficient of diode capacitance  $TC_c = f(V_R)$** **Q factor  $Q = f(f)$   
 $V_R$  = Parameter**